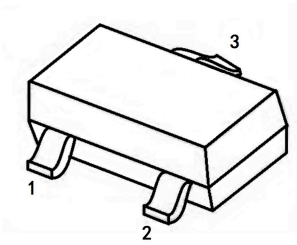
MMBT3906

TRANSISTOR (PNP)

FEATURES

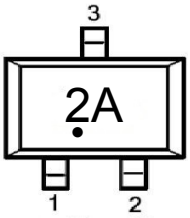
- As complementary type, the NPN transistor MMBT3904 is Recommended
- Epitaxial planar die construction

SOT-23



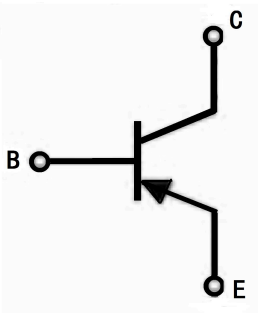
1: B
2: E
3: C

MARKING



Solid dot = Green molding compound device,if none,the normal device.

CIRCUIT DIAGRAM



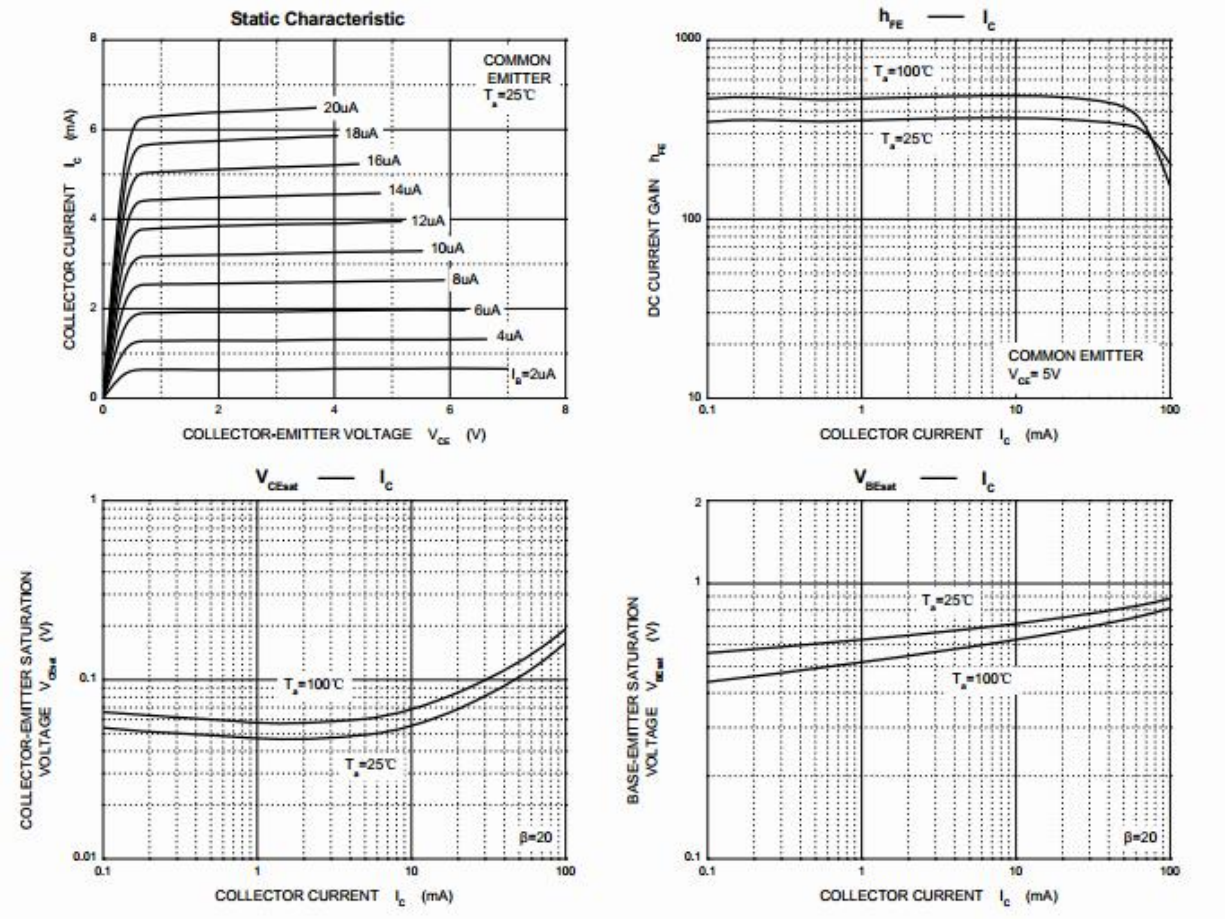
MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_{CM}	-0.1	A
Power Dissipation	P_D	0.45	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55~150	℃

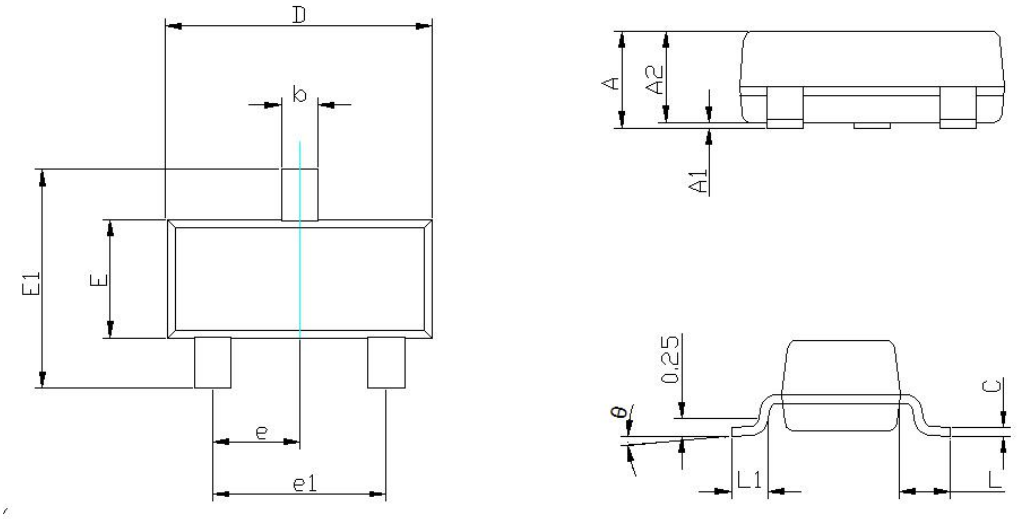
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise spspecified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Emitter-base breakdown voltage	BV_{EBO}	I_E=100uA, I_C=0	-5		V
Collector-base breakdown voltage	BV_{CBO}	I_C=100uA, I_E=0	-50		V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=100uA, I_B=0	-45		V
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0		-0.1	uA
Collector cut-off current	I_{CBO}	V_{CB}=-50V, I_E=0		-0.1	uA
Collector cut-off current	I_{CEO}	V_{CE}=-45V, I_B=0		-0.1	uA
Collector-emitter saturation voltage	V_{CESAT}	I_C=-100mA, I_B=-5mA		-0.3	V
Base-emitter saturation voltage	V_{BESAT}	I_C=-100mA, I_B=-5mA		-1.1	V
DC current gain	h_{FE}	V_{CE}=-5V, I_C=-1mA	100	300	
Transition frequency	f_T	V_{CE}=-5V, I_C=-10m A F=30MHZ	150		MHZ

TYPICAL CHARACTERISTICS



SOT-23 PACKAGE OUTLINE DRAWING



SYMBOL	MILLIMETERTS		INCHES	
	MIN	MAX	MIN	MAX
A	0.900	1.15	0.035	0.045
A1	0.000	0.125	0.000	0.005
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF（0.4-0.6）		0.022REF（0.016-0.024）	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°